Quad D Flip-Flop with Common Clock and Reset

High–Performance Silicon–Gate CMOS

The MC74HC175A is identical in pinout to the LS175. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device consists of four D flip-flops with common Reset and Clock inputs, and separate D inputs. Reset (active-low) is asynchronous and occurs when a low level is applied to the Reset input. Information at a D input is transferred to the corresponding Q output on the next positive going edge of the Clock input.

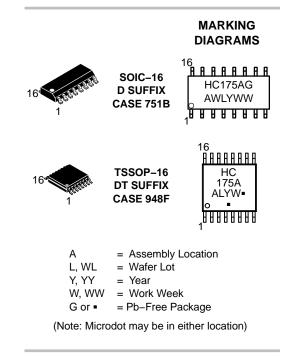
Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7 A
- Chip Complexity 166 FETs or 41.5 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



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ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

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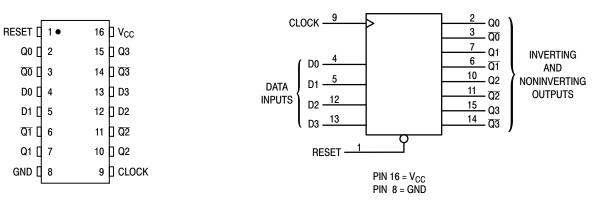


Figure 1. Pin Assignment

Figure 2. Logic Diagram

FUNCTION TABLE

	Inputs			outs
Reset	Clock	D	Q	Q
L	Х	Х	L	Н
Н		Н	н	L
Н		L	L	н
н	L	Х	No Cł	nange

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC175ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HC175ADR2G	SOIC-16 (Pb-Free)	2500 / Tape & Reel
MC74HC175ADTR2G	TSSOP-16 (Pb-Free)	2500 / Tape & Reel
NLV74HC175ADTR2G*	TSSOP-16 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	– 0.5 to + 7.0	V
Vin	DC Input Voltage (Referenced to GND)	-0.5 to V_CC + 0.5	V
Vout	DC Output Voltage (Referenced to GND)	-0.5 to V_CC + 0.5	V
l _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 50	mA
P _D	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature	– 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND $\leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

+Derating - SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)			V _{CC}	V
T _A	Operating Temperature, All Package Types		- 55	+ 125	°C
t _r , t _f	(Figure 1) V _{CC} V _{CC}	= 2.0 V = 3.0 V = 4.5 V = 6.0 V	0 0 0	1000 600 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)
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			Gu	aranteed Li	mit		
Symbol	Parameter	Test Conditions	v _{cc} v	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V _{IH}	Minimum High–Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4 2	V
V _{IL}	Maximum Low–Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.80	0.5 0.9 1.35 1.80	0.5 0.9 1.35 1.80	V
V _{OH}	Minimum High–Level Output Voltage		2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$ \begin{aligned} V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} & I_{\text{out}} \leq 2.4 \text{ m.} \\ I_{\text{out}} \leq 4.0 \text{ m.} \\ I_{\text{out}} \leq 5.2 \text{ m.} \end{aligned} $	A 4.5	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V _{OL}	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$ \begin{array}{ll} V_{in} = V_{IH} \text{ or } V_{IL} & I_{out} \leq 2.4 \text{ m.} \\ I_{out} \leq 4.0 \text{ m.} \\ I_{out} \leq 5.2 \text{ m.} \end{array} $	A 4.5	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
l _{in}	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND	6.0	±0.1	± 1.0	± 1.0	μA
I _{CC}	Maximum Quiescent Supply Current (per Package)		6.0	4	40	160	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

			Guaranteed Limit			
Symbol	Parameter	V _{CC} V	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
f _{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4)	2.0 3.0 4.5 6.0	6 10 30 35	4.8 8.0 24 28	4 6 20 24	MHz
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Clock to Q or Q (Figures 1 and 4)	2.0 3.0 4.5 6.0	150 75 26 22	190 90 32 28	225 110 38 33	ns
t _{PHL}	Maximum Propagation Delay, Reset to Q or Q (Figures 2 and 4)	2.0 3.0 4.5 6.0	125 70 22 19	155 85 27 24	190 110 34 30	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 4)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns
C _{in}	Maximum Input Capacitance	—	10	10	10	pF
			Typical @ 25°C, V_{CC} = 5.0 V			
C _{PD}	Power Dissipation Capacitance (Per Flip-Flop)*			35		pF

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

* Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

TIMING REQUIREMENTS (Input t_r = t_f = 6 ns)

			Gu	aranteed Li	mit	
Symbol	Parameter	v _{cc} v	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
t _{su}	Minimum Setup Time, Data to Clock (Figure 3)	2.0 3.0 4.5 6.0	100 45 20 17	125 65 25 21	150 85 30 26	ns
t _h	Minimum Hold Time, Clock to Data (Figure 3)	2.0 3.0 4.5 6.0	5 3 3 3	5 3 3 3	5 3 3 3	ns
t _{rec}	Minimum Recovery Time, Reset Inactive to Clock (Figure 2)	2.0 3.0 4.5 6.0	100 45 20 17	125 65 25 21	150 85 30 26	ns
t _w	Minimum Pulse Width, Clock (Figure 1)	2.0 3.0 4.5 6.0	80 45 16 14	100 65 20 17	120 85 24 20	ns
t _w	Minimum Pulse Width, Reset (Figure 2)	2.0 3.0 4.5 6.0	80 45 16 14	100 65 20 17	120 85 24 20	ns
t _r , t _f	Maximum Input Rise and Fall Times (Figure 1)	2.0 3.0 4.5 6.0	1000 800 500 400	1000 800 500 400	1000 800 500 400	ns

SWITCHING WAVEFORMS

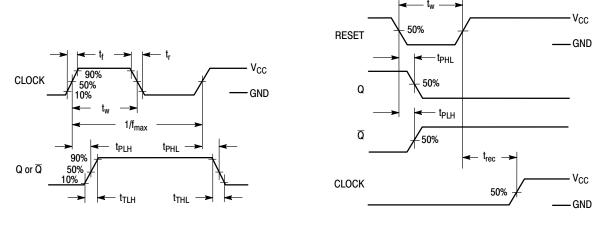
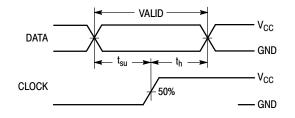


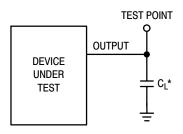
Figure 3.







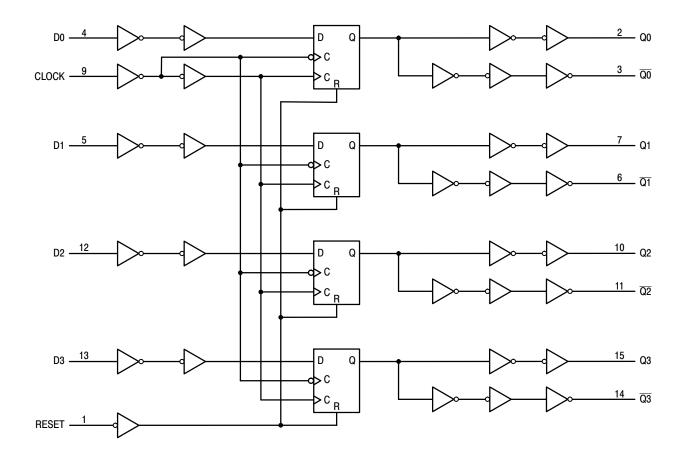




*Includes all probe and jig capacitance

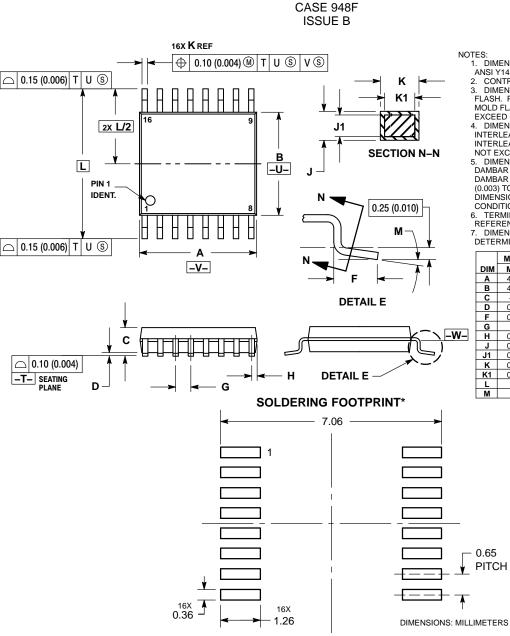
Figure 6.

EXPANDED LOGIC DIAGRAM



PACKAGE DIMENSIONS

TSSOP-16



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

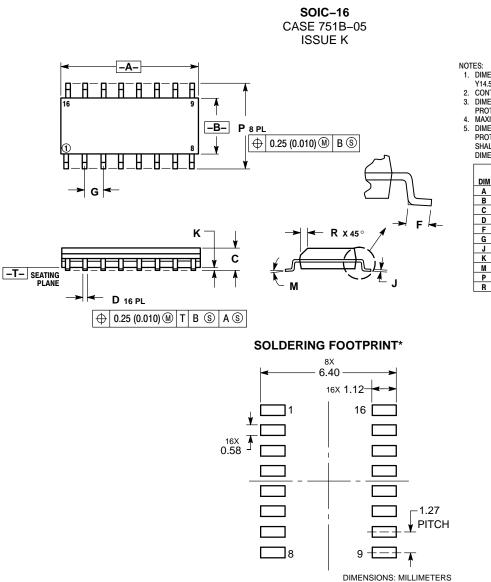
DIMENSIONING AND FOLLERANGING FEA ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: MILLIMETER.
DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS.

FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
κ	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40		0.252 BSC	
М	0 °	8 °	0 °	8 °

PACKAGE DIMENSIONS



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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- Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD
 - 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050) BSC	
J	0.19	0.25	0.008	0.009	
Κ	0.10	0.25	0.004	0.009	
М	0 °	7°	0 °	7°	
Ρ	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	